

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	918	(hybrid adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:29
L2	267	(hybrid adj substrate) and (crystal or crystalline or crystallographic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:31
L3	26	(hybrid adj substrate) and (crystal or crystalline or crystallographic) and (hydrophilic or hydrophobic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:34
L4	89	(first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) with orientation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:36
L5	32	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) with orientation). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:36
L6	3	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) with orientation). clm. and (hydrophilic or hydrophobic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:37
L7	3	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) same (crystal or crystalline or crystallographic) same orientation).clm. and (hydrophilic or hydrophobic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:37
L8	4	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) same (crystal or crystalline or crystallographic) same orientation) and (hydrophilic or hydrophobic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:37

L9	39	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) same (crystal or crystalline or crystallographic) same orientation).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:37
L10	36	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) same orientation).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:38
L11	32	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) with orientation). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:41
L12	3	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) with orientation). clm. and (hydrophilic or hydrophobic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:42
L13	4	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) with orientation) and (hydrophilic or hydrophobic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:43
L14	35	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) with orientation) and bulk	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:43
L15	17	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) with orientation). clm. and bulk	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:43
L16	3	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) with orientation). clm. and bulk.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:44

L17	0	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) with orientation) same bulk	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:45
L18	35	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) with orientation) and bulk	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:47
L19	23	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) with orientation) and bulk and isolation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:47
L20	0	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) with orientation) same substrate same hybrid same isolation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:48
L21	7	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) with orientation) same hybrid	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:48
L22	0	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) with orientation) same substrate same isolation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:49
L23	49	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) with orientation) same substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:49
L24	45	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) with orientation with substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:49

L25	15	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) with orientation with substrate).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:53
L26	45	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) with orientation with substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:55
L27	19	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) with orientation) and ((business adj machines) or ibm)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:56
L28	3	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) with orientation) and ((business adj machines) or ibm) and (hydrophobic or hydrophilic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:57
L29	4	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) with (crystal or crystalline or crystallographic) with orientation) and (hydrophobic or hydrophilic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:58
L30	8	((first or second or upper or lower or top or bottom) same (semiconductor adj layer) with (crystal or crystalline or crystallographic) same orientation) and (hydrophobic or hydrophilic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:59
L31	11	((first or second or upper or lower or top or bottom) same (semiconductor adj layer) same (crystal or crystalline or crystallographic) same orientation) and (hydrophobic or hydrophilic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 13:59
L32	3	((first or second or upper or lower or top or bottom) same (semiconductor adj layer) same (crystal or crystalline or crystallographic) same orientation) and (hydrophobic or hydrophilic) same (bond or bonding or bonded) same surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:00

L33	33	((first or second or upper or lower or top or bottom) same (semiconductor adj layer) same (crystal or crystalline or crystallographic) same orientation) and (ion or ionic or hydrophobic or hydrophilic) same (bond or bonding or bonded) same surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:00
L34	19	((first or second or upper or lower or top or bottom) same (semiconductor adj layer) same (crystal or crystalline or crystallographic) same orientation) and (ion or ionic or hydrophobic or hydrophilic) with (bond or bonding or bonded) same surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:00
L35	11	((first or second or upper or lower or top or bottom) same (semiconductor adj layer) same (crystal or crystalline or crystallographic) same orientation) and (ion or ionic or hydrophobic or hydrophilic) with (bond or bonding or bonded) with surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:03
L36	35	((first or second or upper or lower or top or bottom) same (semiconductor adj layer) same (crystal or crystalline or crystallographic) same orientation) and (etch or etching or clean or cleaning or cleaned or plasma or ion or ionic or hydrophobic or hydrophilic) with (bond or bonding or bonded) with surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:03
L37	4	((first or second or upper or lower or top or bottom) same (semiconductor adj layer) same (crystal or crystalline or crystallographic) same orientation) same (etch or etching or clean or cleaning or cleaned or plasma or ion or ionic or hydrophobic or hydrophilic) with (bond or bonding or bonded) with surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:05
L38	35	((first or second or upper or lower or top or bottom) same (semiconductor adj layer) same (crystal or crystalline or crystallographic) same orientation) and ((etch or etching or clean or cleaning or cleaned or plasma or ion or ionic or hydrophobic or hydrophilic) with (bond or bonding or bonded) with surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:05

L39	20	((first or second or upper or lower or top or bottom) same (semiconductor adj layer) same (crystal or crystalline or crystallographic) same orientation) and ((etch or etching or clean or cleaning or cleaned or plasma or ion or ionic or hydrophobic or hydrophilic) near10 (bond or bonding or bonded) with surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:05
L40	20	((first or second or upper or lower or top or bottom) same (semiconductor adj layer) same (crystal or crystalline or crystallographic) same orientation) and ((etch or etching or clean or cleaning or cleaned or plasma or ion or ionic or hydrophobic or hydrophilic) near10 (bond or bonding or bonded) near10 surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:06
L41	23	((first or second or upper or lower or top or bottom) same (semiconductor adj layer) same (crystal or crystalline or crystallographic) same orientation) and ((etch or etching or clean or cleaning or cleaned or plasma or ion or ionic or hydrophobic or hydrophilic or treat or treating or treatment or treated) near10 (bond or bonding or bonded) near10 surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:12
L42	16	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) same (crystal or crystalline or crystallographic) same orientation) and ((etch or etching or clean or cleaning or cleaned or plasma or ion or ionic or hydrophobic or hydrophilic or treat or treating or treatment or treated) near10 (bond or bonding or bonded) near10 surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:18

L43	7	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) same (crystal or crystalline or crystallographic) same orientation) and ((etch or etching or clean or cleaning or cleaned or plasma or ion or ionic or hydrophobic or hydrophilic or treat or treating or treatment or treated) near5 (bond or bonding or bonded) near5 surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:20
L44	67	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) same (crystal or crystalline or crystallographic) same orientation) and ((etch or etching or clean or cleaning or cleaned or plasma or ion or ionic or hydrophobic or hydrophilic or treat or treating or treatment or treated) near5 surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:22
L45	69	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) same (crystal or crystalline or crystallographic) same orientation) and ((etch or etching or clean or cleaning or cleaned or plasma or ion or ionic or hydrophobic or hydrophilic or treat or treating or treatment or treated or hydrogen or oh) near5 surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:22
L46	13	((first or second or upper or lower or top or bottom) near (semiconductor adj layer) same (crystal or crystalline or crystallographic) same orientation) same ((etch or etching or clean or cleaning or cleaned or plasma or ion or ionic or hydrophobic or hydrophilic or treat or treating or treatment or treated or hydrogen or oh) near5 surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:29

L47	68	(US-20010014514-\$ or US-20010038108-\$ or US-20010047930-\$ or US-20020076902-\$ or US-20020171080-\$ or US-20030038325-\$ or US-20040075141-\$ or US-20040087109-\$ or US-20040151917-\$ or US-20040195646-\$ or US-20040238851-\$ or US-20040256700-\$ or US-20050045995-\$ or US-20050056836-\$ or US-20050070077-\$ or US-20050082531-\$ or US-20050093077-\$ or US-20050093104-\$ or US-20050116290-\$ or US-20020137249-\$ or US-20030057491-\$ or US-20030197166-\$ or US-20040048091-\$ or US-20050009306-\$ or US-20050110419-\$ or US-20050181549-\$).did. or (US-20050217560-\$).did. or (US-5029987-\$ or US-5232789-\$ or US-5279686-\$ or US-5304357-\$ or US-5528054-\$ or US-5654583-\$ or US-5661316-\$ or US-5986734-\$ or US-6015737-\$ or US-6120917-\$ or US-6261928-\$ or US-6387548-\$ or US-6504176-\$ or US-6607641-\$ or US-6689497-\$ or US-6717202-\$ or US-6759277-\$ or US-6784071-\$ or US-6790541-\$ or US-6815278-\$ or US-6830962-\$ or US-5360986-\$ or US-6821826-\$ or US-6902962-\$ or US-6548382-\$ or US-6890838-\$).did. or (GB-2247346-\$).did. or (JP-04338631-\$ or JP-2001044494-\$ or JP-2001068708-\$).did. or (US-5304357-\$ or EP-664557-\$ or US-20040075141-\$ or US-20040195646-\$ or EP-1515373-\$ or US-20050070077-\$ or US-20050082531-\$ or US-20050093077-\$ or US-20050093104-\$ or US-20040256700-\$ or US-6815278-\$).did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/21 14:29
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L48	8	I47 and (bonding adj interface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:30
L49	15	I47 and ((bond or bonding or bonded) near2 interface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:31
L50	18	I47 and ((bond or bonding or bonded) near5 interface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:31
L51	3	I47 and ((bond or bonding or bonded) near5 interface near5 (conductive or conducting))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:32
L52	0	I47 and ((bond or bonding or bonded) near5 interface near5 (conductive or conducting) near5 surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:32
L53	2	I47 and ((bond or bonding or bonded) near10 interface near10 (conductive or conducting) near10 surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:32
L54	191	((bond or bonding or bonded) near10 interface near10 (conductive or conducting) near10 surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:33
L55	4	((crystal or crystallographic or crystalline) near2 orientation) and ((bond or bonding or bonded) near10 interface near10 (conductive or conducting) near10 surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:33
L56	164	((crystal or crystallographic or crystalline) near2 orientation) and ((bond or bonding or bonded) near10 (conductive or conducting) near10 surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:33
L57	17	((crystal or crystallographic or crystalline) near2 orientation) same ((bond or bonding or bonded) near10 (conductive or conducting) near10 surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:34

L58	14123	((bond or bonding or bonded) near10 (conductive or conducting) near10 surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:34
L59	890	((bond or bonding or bonded) near10 (conductive or conducting) near10 surface) and hybrid	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:34
L60	17	((bond or bonding or bonded) near10 (conductive or conducting) near10 surface) and hybrid and ((crystal or crystalline or crystallographic) near orientation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:34

L64	24	l63 and (conducting or conductive)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:36
L65	20	(hybrid or soi) same (crystal or crystalline or crystallographic) same (semiconductor adj layer) same (bond or bonding or bonded) same (metal or conductive or conducting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:45
L66	12	(hybrid or soi) same (crystal or crystalline or crystallographic) same (semiconductor adj layer) same (bond or bonding or bonded) same (metal or conductive or conducting) same surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:47
L67	13	(hybrid or soi) same (crystal or crystalline or crystallographic) same (semiconductor adj layer) same (bond or bonding or bonded) same (metal or conductive or conducting or conductor) same surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:50
L68	3	(hybrid or soi) same (crystal or crystalline or crystallographic) same (semiconductor adj layer) same (bond or bonding or bonded) same (metal or conductive or conducting or conductor) same surface same interface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:50
L69	9	(crystal or crystalline or crystallographic) same (semiconductor adj layer) same (bond or bonding or bonded) same (metal or conductive or conducting or conductor) same surface same interface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/21 14:50